AMENDMENTS TO THE SPECIFICATION

In the Title:

Delete the phrase "Method Of Making A" at the beginning of the title.

In the Background of the Invention:

Amend paragraph [0006] as follows:

[0006] Relatively recently, a new sort of DG MOSFET has been introduced in conjunction with silicon on insulator (SOI) technology that overcomes some of the drawbacks of planar DG MOSFETs. As seen in FIG. 1A, this new DG MOSFET 10 is formed vertically rather than horizontally and has been given the name finFET, since the structure 12 that contains each pair of source 14 and drain 18 resembles a fin. As mentioned, finFET 10 is typically made using a SOI wafer 22 that includes a buried oxide (BOX) layer 26 sandwiched between a silicon lower layer 30 and a silicon upper layer 34. In the case of finFET 10, much of upper layer 34 has been etched away to define two parallel fins 12 that each form one source 14, one drain 18 and a channel 42 (FIG. 1B) between the source and drain. After fins 12 have been formed, subsequent processing steps include forming a gate oxide (not shown) on fins 12 and forming gate 46, which is common to both fins. Once gate 46 has been formed, sources 14 and drains 18 are doped, as illustrated by arrows 50, to achieve the proper doping. Doping is typically done using ion implantation from the front side of wafer 22, typically at an angle of about 30 degrees relative to a normal from the wafer so that ions can enter each fin 12 along its entire height without interference from an adjacent fin.

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